

TOSHIBA**TA8312F**

TENTATIVE

TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MULTI CHIP

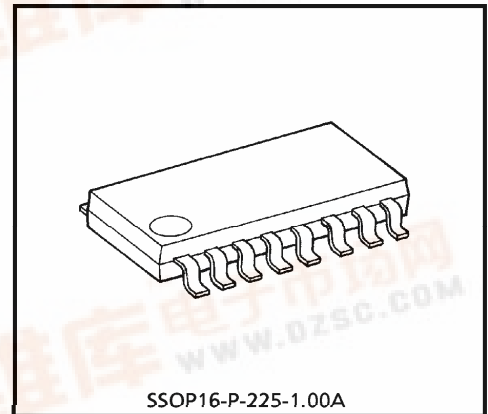
TA8312F**MOTOR DRIVER FOR CAMERA**

TA8312F is Multi Chip IC incorporates 6 low saturation discrete transistors which equipped bias resistor and Free-Wheeling diode.

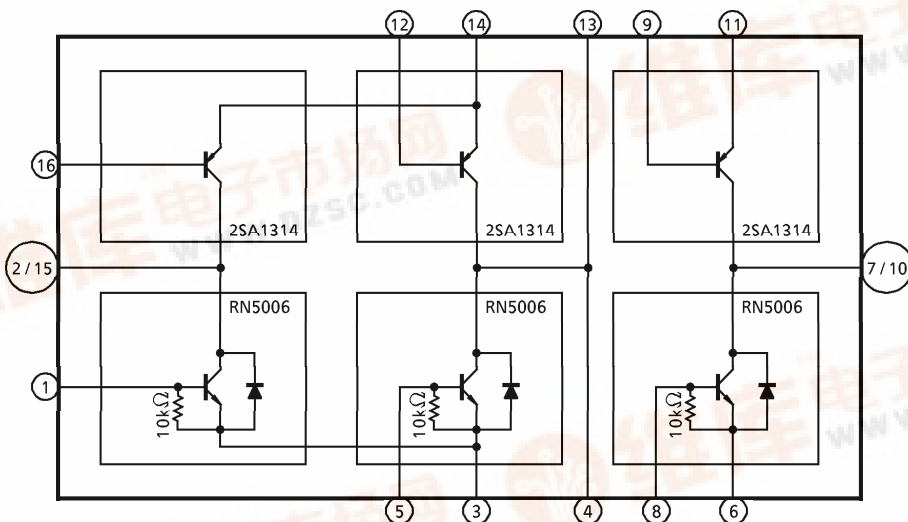
This IC is suitable for a camera use motor drive applications.

FEATURES

- Suitable for high efficiency motor drive circuit.
- Built-in Bias Resistor : $R = 10k\Omega$
- Built-in Free-Wheeling diode
- Small package sealed : SSOP16
- Low saturation voltage



Weight : 0.14g (Typ.)

BLOCK DIAGRAM

980910EBA2

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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	10	V
Breakdown Voltage	V _{CBO}	10	V
	V _{CEO}	10	V
	V _{EBO}	6	V
Output Current	I _{OUT}	2	A
Base Current	I _B	0.4	A
Power Dissipation	P _D	330	mW
Junction Temperature	T _j	150	°C
Operating Temperature	T _{opr}	- 20~60	°C
Storage Temperature	T _{stg}	- 55~150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	MEASURING Tr	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Gain	h _{FE} 1	2SA1314	—	V _{CE} = - 1V, I _C = - 0.5A	140	—	600	
	h _{FE} 2	RN5006	—	V _{CE} = 1V, I _C = 0.5A	160	—	600	
Saturation Voltage	V _{CE} 1	2SA1314	—	I _C = - 2A, I _B = - 50mA	- 0.5	—	—	V
	V _{CE} 2	RN5006	—	I _C = 2A, I _B = 50mA	—	—	0.5	V
Output Leak Current	I _{OFF}		—	V _{CC} = 7V	—	—	1.0	μA
Input Resistance	R	RN5006	—		7	10	13	kΩ
Diode Forward Voltage	V _F	RN5006	—	I _F = 300mA	—	0.89	1.2	V
Transition Frequency	f _{T1}	2SA1314	—	V _{CE} = - 1V, I _C = - 0.5A	—	140	—	MHz
	f _{T2}	RN5006	—	V _{CE} = 1V, I _C = 0.5A	—	140	—	MHz

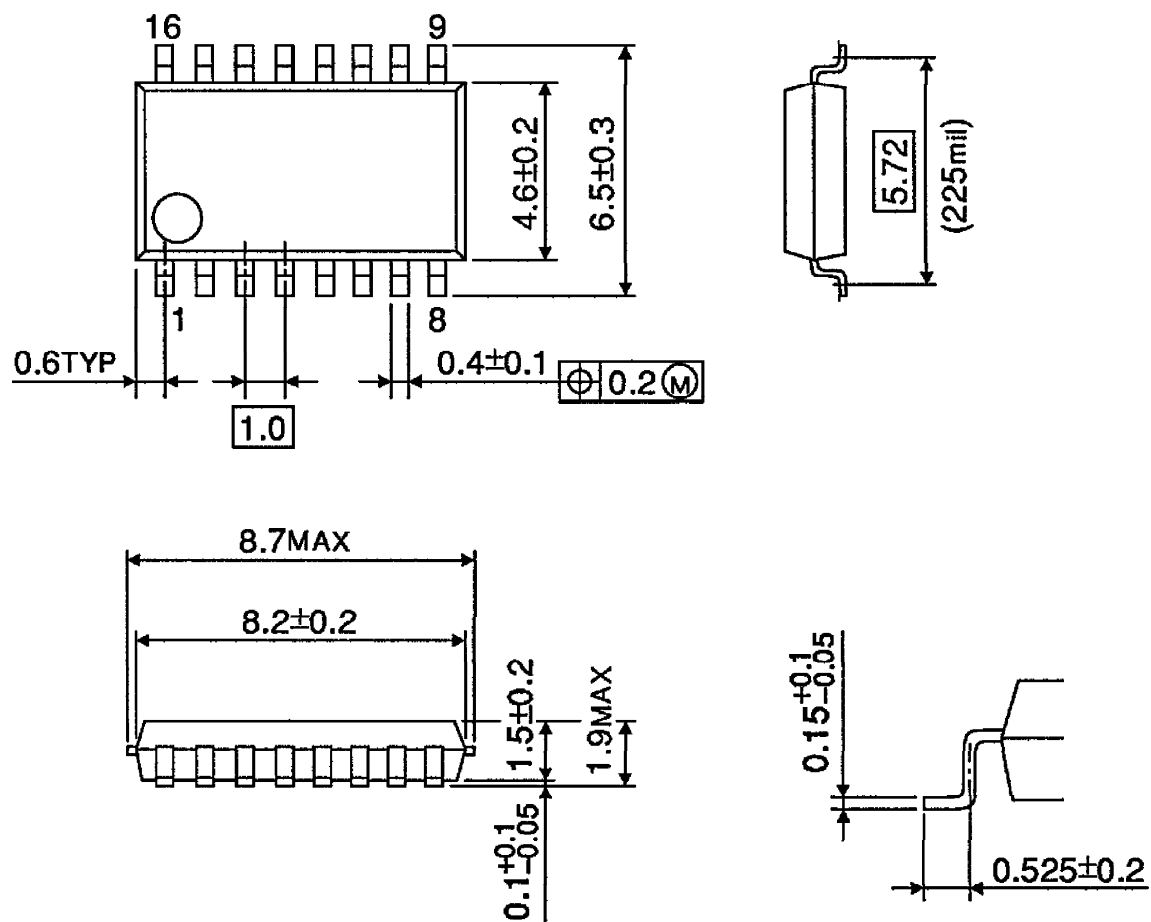
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OUTLINE DRAWING

SSOP16-P-225-1.00A

Unit : mm



Weight : 0.14g (Typ.)